

General Description

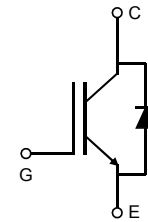
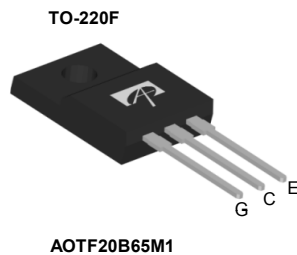
- Latest Alpha IGBT (α IGBT) technology
- 650V breakdown voltage
- Very fast and soft recovery freewheeling diode
- High efficient turn-on di/dt controllability
- Low $V_{CE(sat)}$ enables high efficiencies
- Low turn-off switching loss and softness
- Very good EMI behavior
- High short-circuit ruggedness

Applications

- Motor Drives
- Sewing Machines
- Home Appliances
- Fan, Pumps, Vacuum Cleaner
- Other Hard Switching Applications

Product Summary

V_{CE}	650V
I_C ($T_C=100^\circ\text{C}$)	20A
$V_{CE(sat)}$ ($T_J=25^\circ\text{C}$)	1.7V



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOTF20B65M1	TO220F	Tube	1000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOTF20B65M1	Units
Collector-Emitter Voltage	V_{CE}	650	V
Gate-Emitter Voltage	V_{GE}	± 30	V
Continuous Collector Current	I_C	$T_C=25^\circ\text{C}$	40 ²⁾
		$T_C=100^\circ\text{C}$	20 ²⁾
Pulsed Collector Current, Limited by T_{Jmax}	I_{CM}	60	A
Turn off SOA, $V_{CE} \leq 650\text{V}$, Limited by T_{Jmax}	I_{LM}	60	A
Continuous Diode Forward Current	I_F	$T_C=25^\circ\text{C}$	40 ²⁾
		$T_C=100^\circ\text{C}$	20 ²⁾
Diode Pulsed Current, Limited by T_{Jmax}	I_{FM}	60	A
Short circuit withstanding time ¹⁾ $V_{GE}=15\text{V}$, $V_{CC} \leq 400\text{V}$, $T_J \leq 150^\circ\text{C}$	t_{SC}	5	μs
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	45
		$T_C=100^\circ\text{C}$	18
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOTF20B65M1	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	65	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	2.8	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	3.7	$^\circ\text{C/W}$

1) Allowed number of short circuits: <1000; time between short circuits: >1s.

2) TO220F I_C follows TO220/TO263.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C=1mA, V_{GE}=0V, T_J=25^\circ C$	650	-	-	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=20A$	$T_J=25^\circ C$	-	1.7	2.15	V
			$T_J=125^\circ C$	-	2.02	-	
			$T_J=150^\circ C$	-	2.11	-	
V_F	Diode Forward Voltage	$V_{GE}=0V, I_C=20A$	$T_J=25^\circ C$	-	1.66	2.1	V
			$T_J=125^\circ C$	-	1.67	-	
			$T_J=150^\circ C$	-	1.65	-	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=5V, I_C=1mA$	-	5.1	-	V	
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=650V, V_{GE}=0V$	$T_J=25^\circ C$	-	-	10	μA
			$T_J=125^\circ C$	-	-	500	
			$T_J=150^\circ C$	-	-	1000	
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0V, V_{GE}=\pm 30V$	-	-	±100	nA	
g_{FS}	Forward Transconductance	$V_{CE}=20V, I_C=20A$	-	14	-	S	
DYNAMIC PARAMETERS							
C_{ies}	Input Capacitance	$V_{GE}=0V, V_{CC}=25V, f=1MHz$	-	1212	-	pF	
C_{oes}	Output Capacitance		-	141	-	pF	
C_{res}	Reverse Transfer Capacitance		-	50	-	pF	
Q_g	Total Gate Charge	$V_{GE}=15V, V_{CC}=520V, I_C=20A$	-	46	-	nC	
Q_{ge}	Gate to Emitter Charge		-	12	-	nC	
Q_{gc}	Gate to Collector Charge		-	21	-	nC	
$I_{C(SC)}$	Short circuit collector current	$V_{GE}=15V, V_{CC}=400V,$ $t_{sc} \leq 5\mu s, T_J \leq 150^\circ C$	-	115	-	A	
R_g	Gate resistance	$V_{GE}=0V, V_{CC}=0V, f=1MHz$	-	13	-	Ω	
SWITCHING PARAMETERS, (Load Inductive, T_J=25°C)							
$t_{D(on)}$	Turn-On Delay Time	$T_J=25^\circ C$ $V_{GE}=15V, V_{CC}=400V, I_C=20A,$ $R_G=15\Omega$	-	26	-	ns	
t_r	Turn-On Rise Time		-	25	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	122	-	ns	
t_f	Turn-Off Fall Time		-	13	-	ns	
E_{on}	Turn-On Energy		-	0.47	-	mJ	
E_{off}	Turn-Off Energy		-	0.27	-	mJ	
E_{total}	Total Switching Energy		-	0.74	-	mJ	
t_{rr}	Diode Reverse Recovery Time		$T_J=25^\circ C$	-	322	-	ns
Q_{rr}	Diode Reverse Recovery Charge		$I_F=20A, di/dt=200A/\mu s, V_{CC}=400V$	-	0.8	-	μC
I_{rm}	Diode Peak Reverse Recovery Current			-	5.2	-	A
SWITCHING PARAMETERS, (Load Inductive, T_J=150°C)							
$t_{D(on)}$	Turn-On Delay Time	$T_J=150^\circ C$ $V_{GE}=15V, V_{CC}=400V, I_C=20A,$ $R_G=15\Omega$	-	24	-	ns	
t_r	Turn-On Rise Time		-	27	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	144	-	ns	
t_f	Turn-Off Fall Time		-	22	-	ns	
E_{on}	Turn-On Energy		-	0.50	-	mJ	
E_{off}	Turn-Off Energy		-	0.43	-	mJ	
E_{total}	Total Switching Energy		-	0.93	-	mJ	
t_{rr}	Diode Reverse Recovery Time		$T_J=150^\circ C$	-	463	-	ns
Q_{rr}	Diode Reverse Recovery Charge		$I_F=20A, di/dt=200A/\mu s, V_{CC}=400V$	-	1.5	-	μC
I_{rm}	Diode Peak Reverse Recovery Current			-	6.7	-	A

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

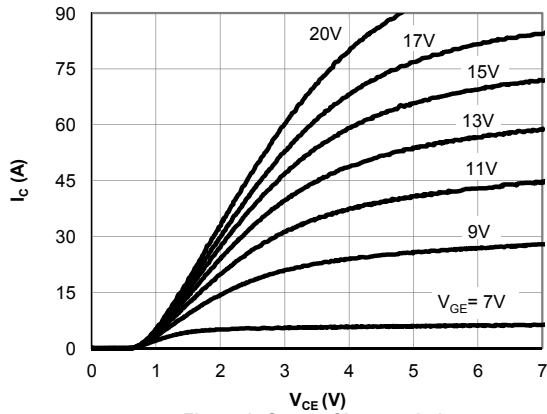


Figure 1: Output Characteristic
($T_j=25^\circ\text{C}$)

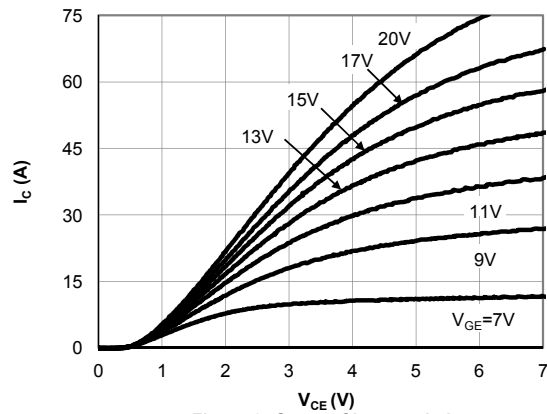


Figure 2: Output Characteristic
($T_j=150^\circ\text{C}$)

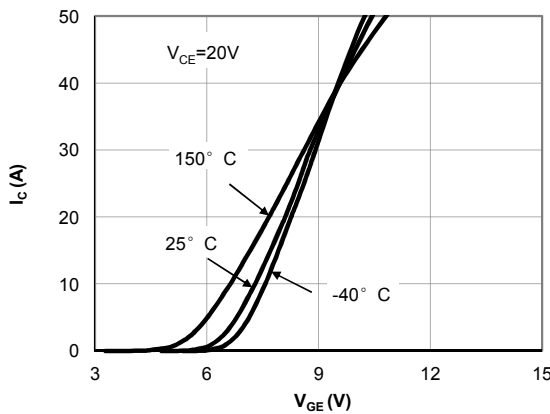


Figure 3: Transfer Characteristic

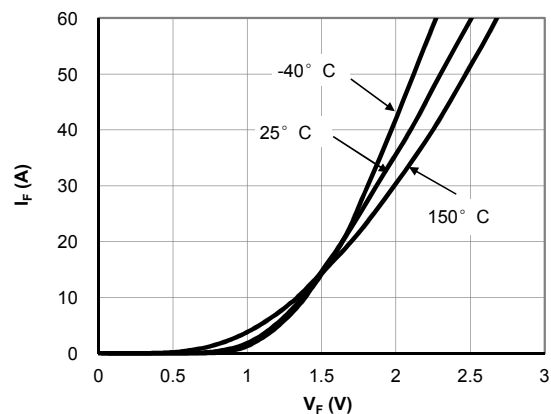


Figure 4: Diode Characteristic

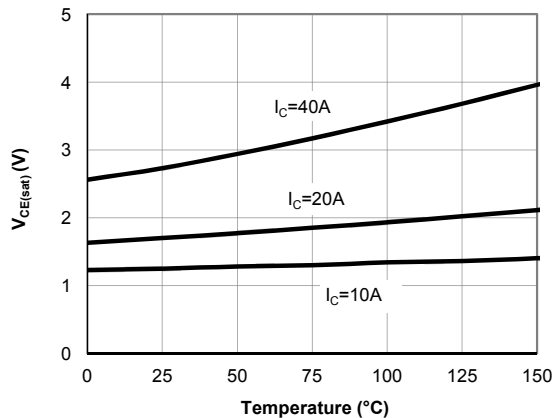


Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

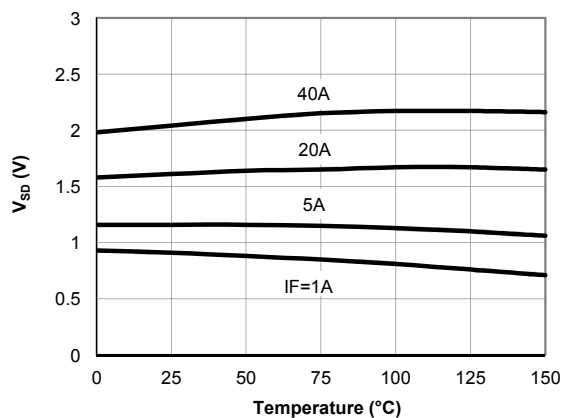


Figure 6: Diode Forward Voltage vs. Junction Temperature

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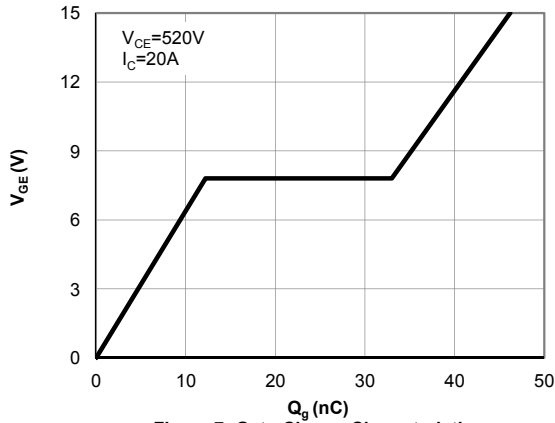


Figure 7: Gate-Charge Characteristics

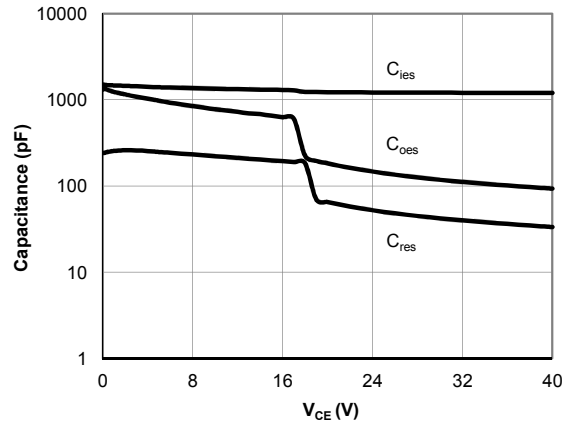


Figure 8: Capacitance Characteristic

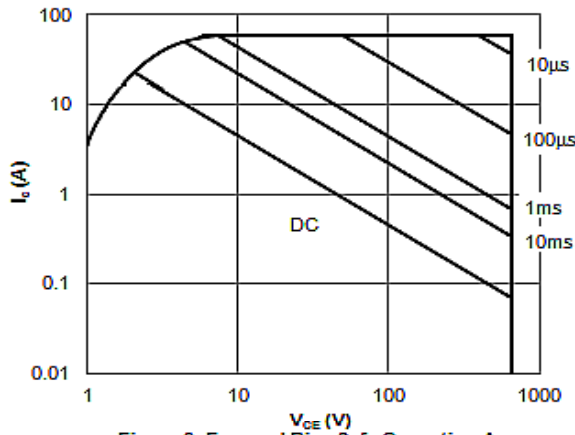


Figure 9: Forward Bias Safe Operating Area
($T_c=25^\circ\text{C}$, $V_{GE}=15\text{V}$)

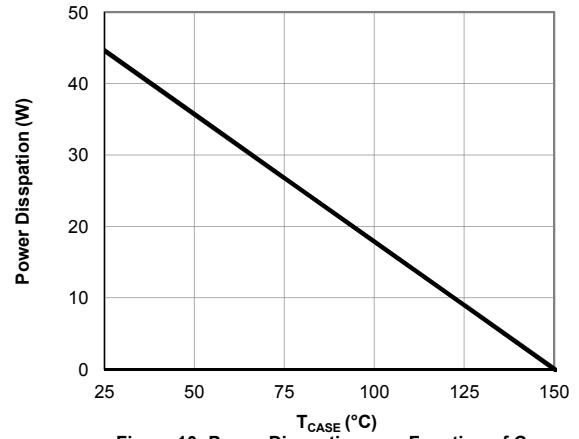


Figure 10: Power Dissipation as a Function of Case

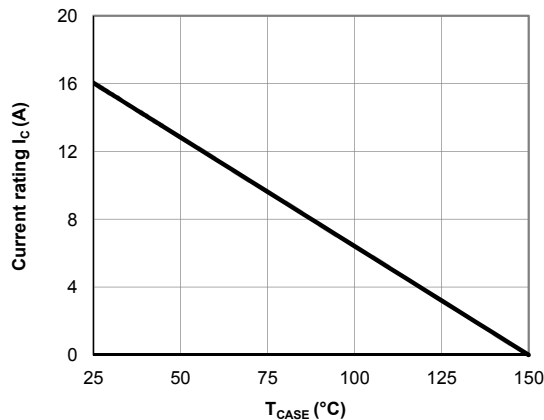


Figure 11: Current De-rating

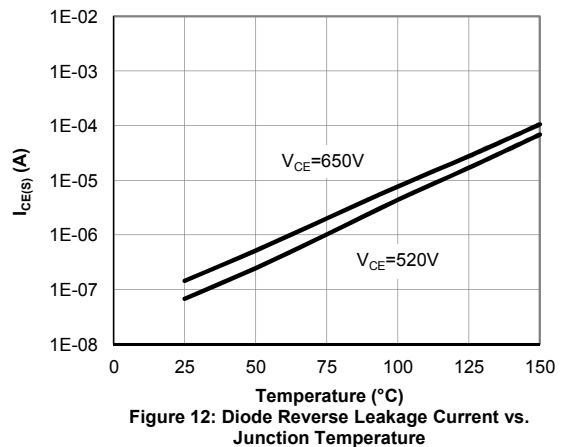
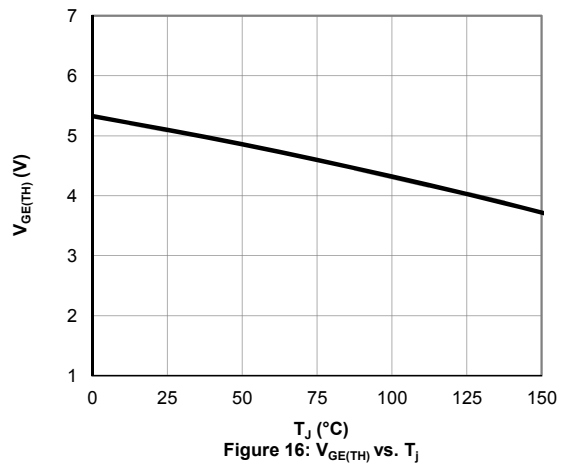
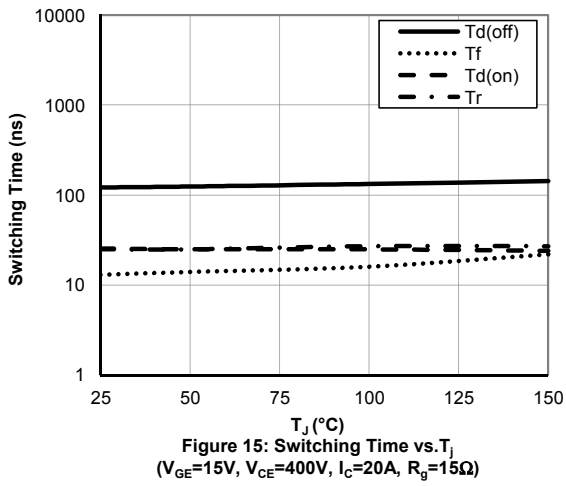
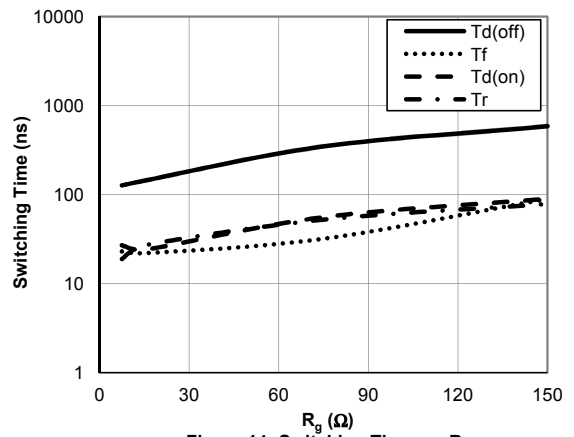
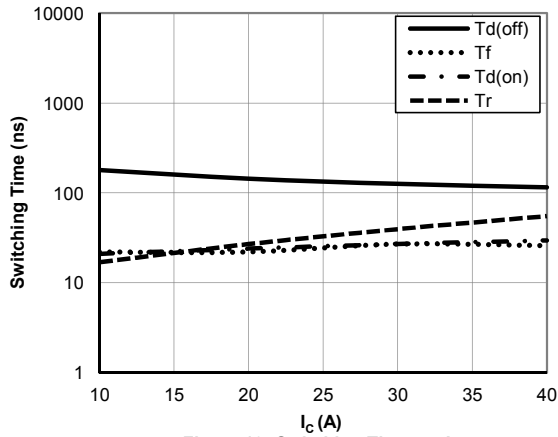


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

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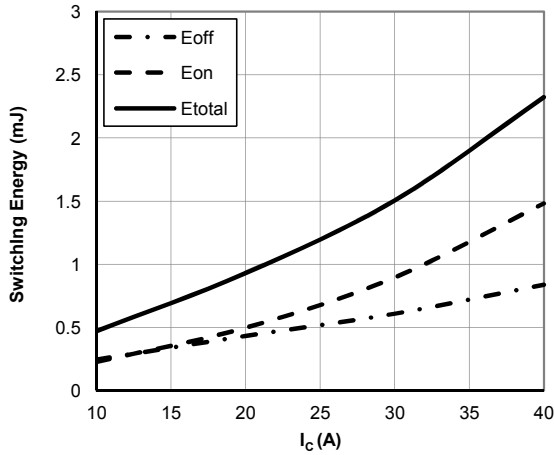


Figure 17: Switching Loss vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=15\Omega$)

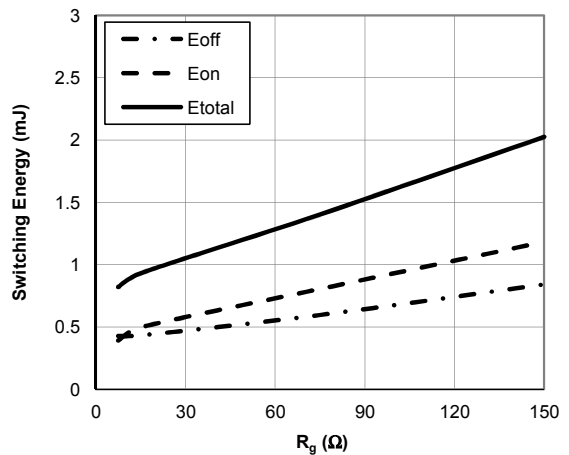


Figure 18: Switching Loss vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$)

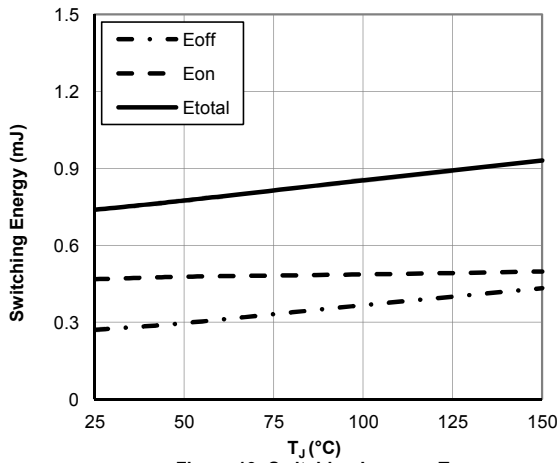


Figure 19: Switching Loss vs. T_J
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$, $R_g=15\Omega$)

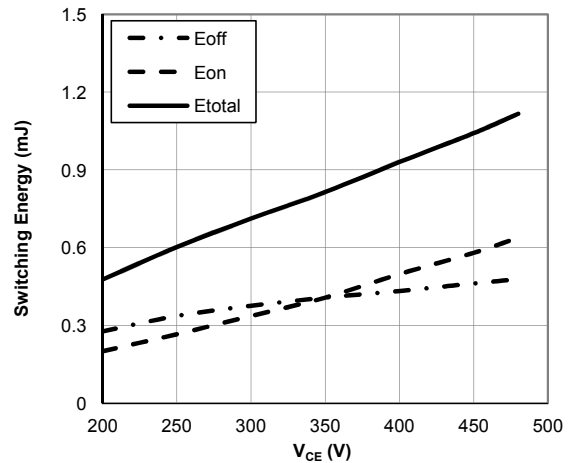


Figure 20: Switching Loss vs. V_{CE}
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=20\text{A}$, $R_g=15\Omega$)

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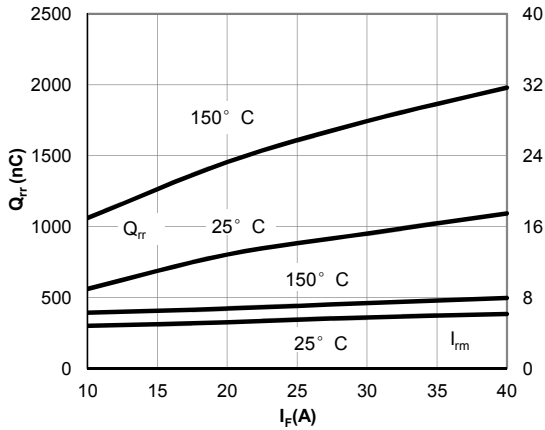


Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
 ($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

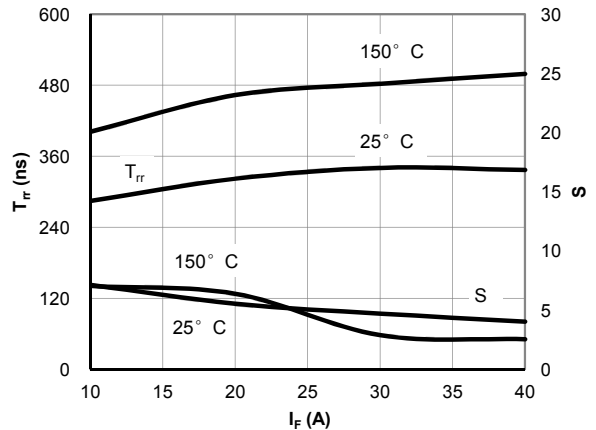


Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
 ($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

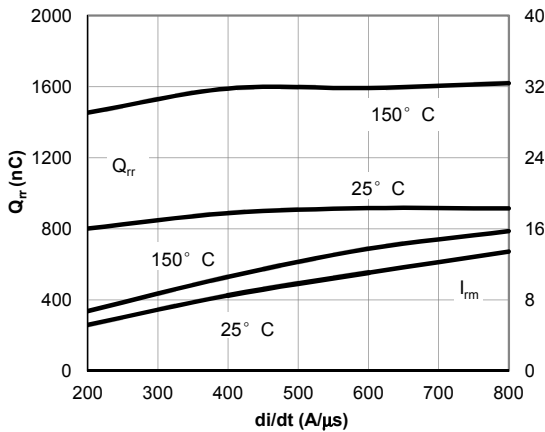


Figure 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
 ($V_{GE}=15V, V_{CE}=400V, I_F=20A$)

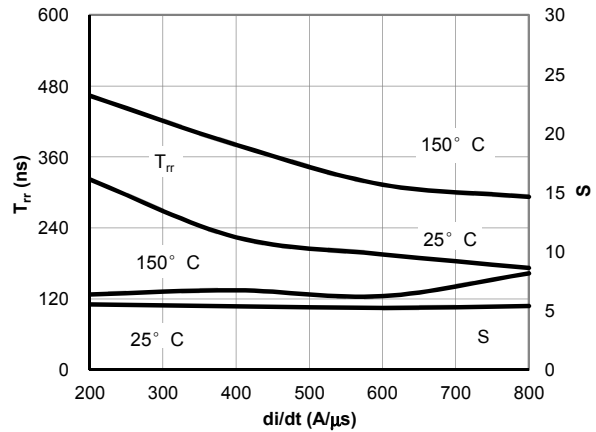


Figure 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
 ($V_{GE}=15V, V_{CE}=400V, I_F=20A$)

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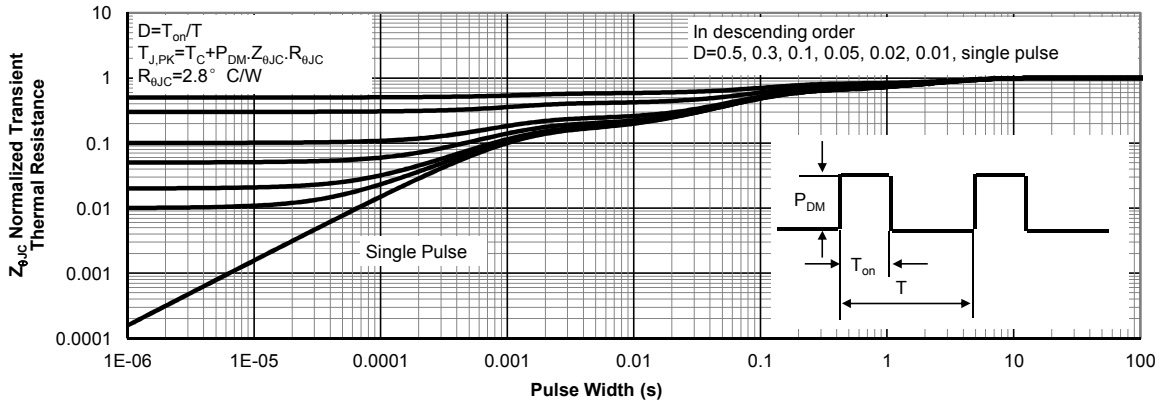


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

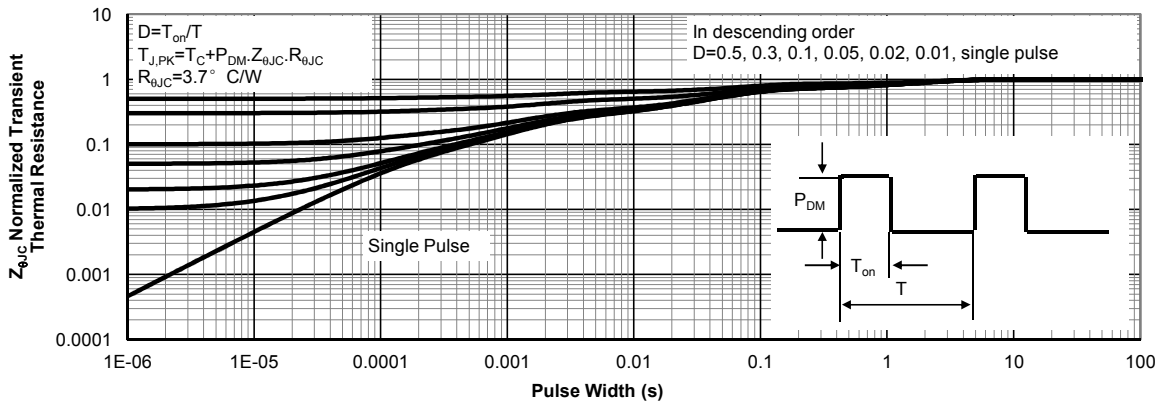


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

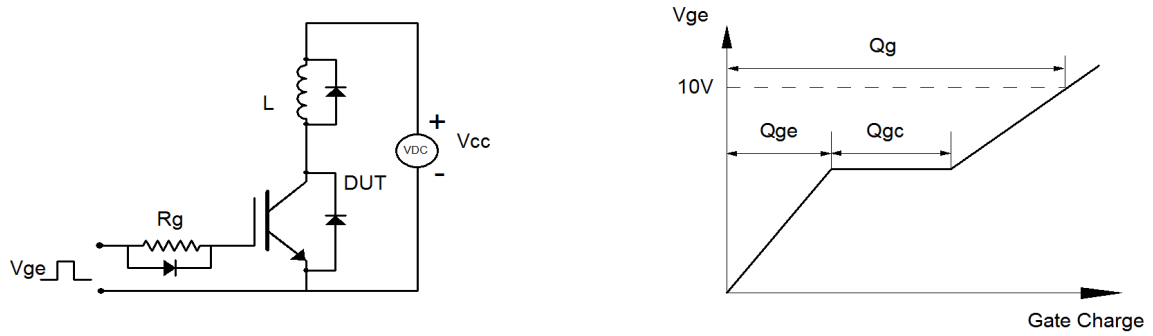


Figure A: Gate Charge Test Circuit & Waveforms

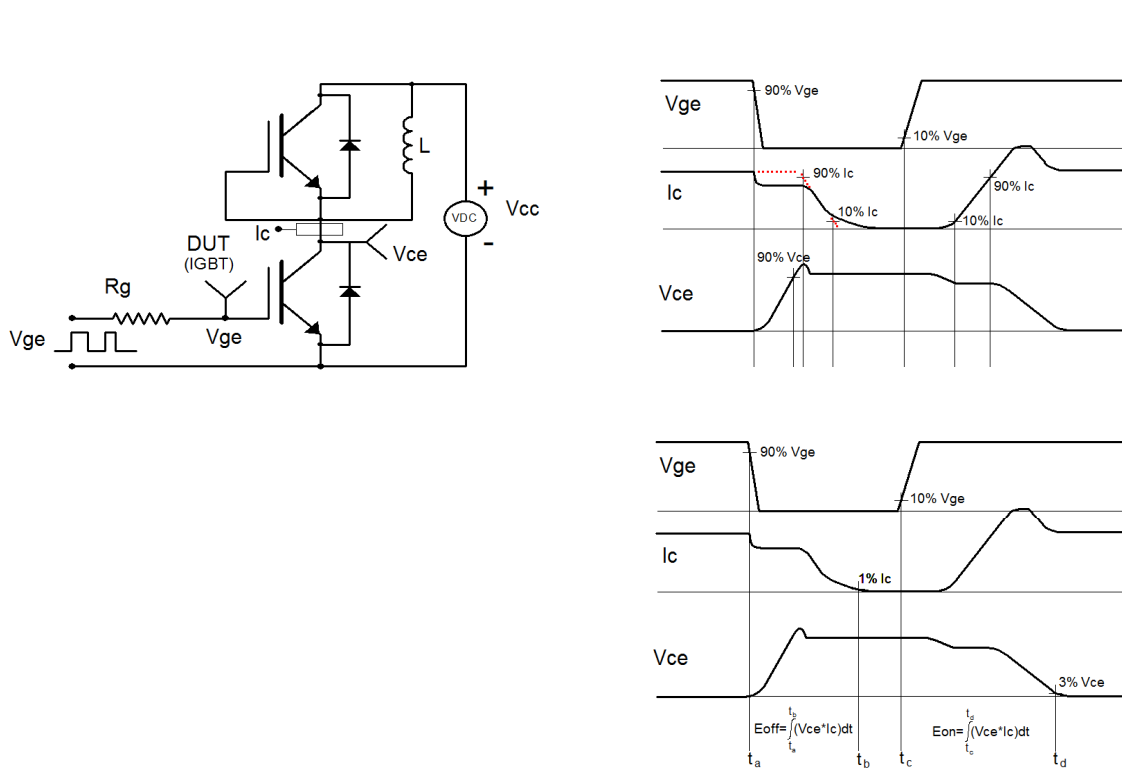


Figure B: Inductive Switching Test Circuit & Waveforms

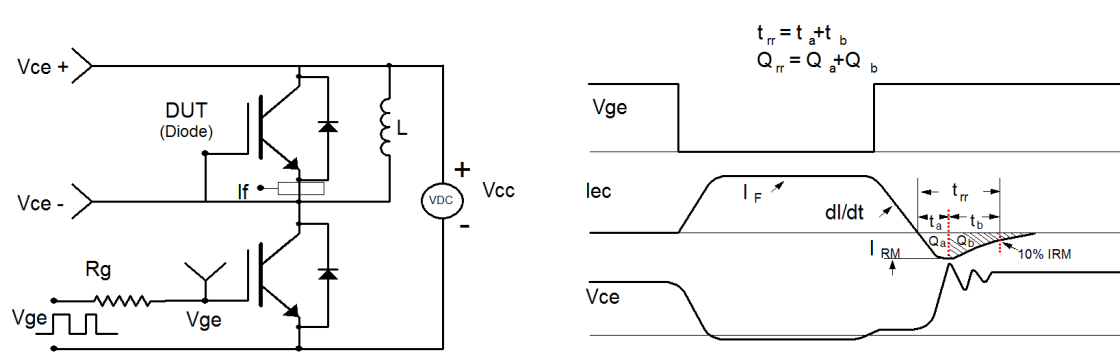


Figure C: Diode Recovery Test Circuit & Waveforms

单击下面可查看定价，库存，交付和生命周期等信息

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